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 MEWS
                  "Ask CAS" for self-help around the clock
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          SEP 09
                  CA/Caplus records now contain indexing from 1907 to the
                  present
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          AUG 05
                  New pricing for EUROPATFULL and PCTFULL effective
                  August 1, 2003
 NEWS
      5
          AUG 13 Field Availability (/FA) field enhanced in BEILSTEIN
 NEWS
     -6
          AUG 18 Data available for download as a PDF in RDISCLOSURE
          AUG 18
                  Simultaneous left and right truncation added to PASCAL
          AUG 18
                  FROSTI and KOSMET enhanced with Simultaneous Left and Righ
                  Truncation
 MEMS
          AUG 18
                  Simultaneous left and right truncation added to ANABSTR
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          SEP 22
                  DIPPR file reloaded
 NEWS 11
          SEP 25
                  INPADOC: Legal Status data to be reloaded
 NEWS 12
          SEP 29 DISSABS now available on STN
 NEWS 13
         OCT 10 PCTFULL: Two new display fields added
               OCTOBER 01 CURRENT WINDOWS VERSION IS V6.01a, CURRENT
 NEWS EXPRESS
               MACINTOSH VERSION IS V6.0b(ENG) AND V6.0Jb(JP),
               AND CURRENT DISCOVER FILE IS DATED 23 SEPTEMBER 2003
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<>< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
    THE BASIC INDEX >>>
=> s phase shift mask
        713679 PHASE
        147036 SHIFT
         21527 MASK
L1
           516 PHASE SHIFT MASK
                 (PHASE (W) SHIFT (W) MASK)
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=> s expession optical system 61904 EXPOSURE

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668960 OPTICAL
       1595550 SYSTEM
             1 EXPOSURE OPTICAL SYSTEM
                 (EXPOSURE (W) OPTICAL (W) SYSTEM)
=> d 12
     ANSWER 1 OF 1 INSPEC (C) 2003 IEE on STN
   Text
AN
     2001:6804707 INSPEC
                              DN B2001-02-2550G-151
ΊΊ
     Influence of electron density distribution at the electron source in a
     projection exposure system.
AU
     Kotera, M.; Sakai, M. (Osaka Inst. of Technol., Japan); Shimizu, I.; Tomo,
     Y.; Yoshida, A.; Kojima, Y.; Yamabe, M.
SO
     Digest of Papers Microprocesses and Nanotechnology 2000. 2000
     International Microprocesses and Nanotechnology Conference (IEEE Cat.
     No. 00EX387)
     Tokyo, Japan: Japan Soc. Appl. Phys, 2000. p.140-1 of xxviii+306 pp. 0
     refs.
     Conference: Tokyo, Japan, 11-13 July 2000
     Sponsor(s): Japan Soc. Appl. Phys.; IEEE Electron Device Soc.; American
     Vacuum Soc.; Assoc. Super-Adv. Electron. Technol.; IEE of Japan; IEICE;
     Japanese Soc. Synchrotron Radiation Res.; Japanese Soc. Electron
     Microscopy; Surface Sci. Soc. Japan; Vacuum Soc. Japan
     ISBN: 4-89114-004-6
     Conference Article
DT
TC
    Theoretical
CY
     Japan
LA
     English
=> a excavation
          871 EXCAVATION
=> s %% and %2
             0 L1 AND L2
1.4
=> g 11 and 13
L5
             0 L1 AND L3
=> s resist pattern
         12602 RESIST
        182954 PATTERN
           424 RESIST PATTERN
                 (RESIST (W) PATTERN)
=> 2 1.1 and 1.6
             7 L1 AND L6
=> 3 17 1-7
     ANSWER 1 OF 7 INSPEC (C) 2003 IEE on STN
   Text
AN
     2003:7717431 INSPEC
                              DN B2003-10-2550G-142
ΤI
     Preliminary study of 65 nm node alternating phase-shift mask fabrication.
וומ
     Hosono, K.; Ishiwata, N.; Asai, S.; Maruyama, H.; Miyahara, Y. (Fujitsu
     Ltd., Tokyo, Japan); Sanki, S.; Yamashita, Y.; Hotta, Y.; Furukawa, T.;
     Naitou, M.; Miyashita, H.; Noguchi, S.
     Proceedings of the SPIE - The International Society for Optical
     Engineering (2002) vol.4889, p.1273-80. 3 refs.
     Published by: SPIE-Int. Soc. Opt. Eng
     Price: CCCC 0277-786X/02/$15.00
```

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CODEN: PSISDG ISSN: 0277-786X
      SICI: 0277-786X(2002)4889L.1273:PSNA;1-Y
      Conference: 22nd Annual BACUS Symposium on Photomask Technology. Monterey,
      CA, USA, 1-4 Oct 2002
      Sponsor(s): SPIE
      Conference Article; Journal
 DT
 TC
      Experimental
 CY
      United States
 LA
      English
     ANSWER 2 OF 7 INSPEC (C) 2003 IEE on STN
 AN
      1998:5803277 INSPEC
                              DN B9802-2550G-201
 ΤI
     Optical proximity correction of alternating phase-shift masks for 0.18 mu
     m KrF lithography.
ΑU
     Yasuzato, T.; Ishida, S. (ULSI Device Dev. Lab., NEC Corp., Sagamihara,
     Japan); Shioiri, S.; Tanabe, H.; Kasama, K.
     Proceedings of the SPIE - The International Society for Optical
     Engineering (1997) vol.3051, p.751-62. 5 refs.
     Published by: SPIE-Int. Soc. Opt. Eng
     Price: CCCC 0277-786X/97/$10.00
     CODEN: PSISDG ISSN: 0277-786X
     SICI: 0277-786X(1997)3051L.751:OPCA;1-0
     Conference: Optical Microlithography X. Santa Clara, CA, USA, 12-14 March
     1997
     Sponsor(s): SPIE
     Conference Article; Journal
DT
TC
     Experimental
CY
     United States
LA
     English
1.7
     ANSWER 3 OF 7 INSPEC (C) 2003 IEE on STN
AN
     1997:5611672 INSPEC
                              DN B9708-2550G-008
TI
     Impact of lens aberrations on optical lithography.
ΑU
     Brunner, T.A. (Microelectron. Div., IBM Corp., East Fishkill, NY, USA)
     IBM Journal of Research and Development (Jan.-March 1997) vol.41, no.1-2,
SO
     p.57-67. 18 refs.
     Published by: IBM
     Price: CCCC 0018-8646/97/$5.00
     CODEN: IBMJAE ISSN: 0018-8646
    SICI: 0018-8646(199701/03)41:1/2L.57:ILAO;1-N
DT
    Journal
TC
    Theoretical
CY
    United States
LA
    English
    ANSWER 4 OF 7 INSPEC (C) 2003 IEE on STN
    Text
    1996:5426662 INSPEC
                             DN B9701-2550G-005; C9701-7410D-002
    Improvement of resist pattern fidelity with partial attenuated phase
    shift mask.
    Yasuzato, T.; Ishida, S.; Kasama, K. (VLSI Dev. Div., NEC Corp.,
    Sagamihara, Japan)
    Proceedings of the SPIE - The International Society for Optical
    Engineering (1996) vol.2726, p.496-507. 12 refs.
    Published by: SPIE-Int. Soc. Opt. Eng
    Price: CCCC 0 8194 2102 2/96/$6.00
    CODEN: PSISDG ISSN: 0277-786X
    SICI: 0277-786X(1996)2726L.496:IRPF;1-Q
    Conference: Optical Microlithography IX. Santa Clara, CA, USA, 13-15 March
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ΤI

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1996

Sponsor(s): SPIE

DT Conference Article: Journal

- Practical; Theoretical; Experimental TC
- CY United States
- LA English
- ANSWER 5 OF 7 INSPEC (C) 2003 IEE on STN

- AN 1995:5082029 INSPEC DN B9512-2550G-016
- ΤI A study of optical proximity effects using off-axis illumination with attenuated phase shift mask.
- Ahn, C.-N.; Baik, K.-H.; Lee, Y.-S.; Kim, H.-E.; Hur, I.-B.; Kim, Y.-S.; Kim, J.-H.; Choi, S.-H. (Semicond. R. & D. Labs., Hyundai Electron. Ind. Co. Ltd., Kyungki-do, South Korea)
- Proceedings of the SPIE The International Society for Optical SO Engineering (1995) vol.2440, p.222-39. 7 refs. Price: CCCC 0 8194 1788 2/95/\$6.00 CODEN: PSISDG ISSN: 0277-786X
 - Conference: Optical/Laser Microlithography VII. Santa Clara, CA, USA, 22-24 Feb 1995
- Sponsor(s): SPIE DT Conference Article; Journal
- Practical: Theoretical: Experimental TC
- CY United States
- LA English

ANSWER 6 OF 7 INSPEC (C) 2003 IEE on STN

- AN 1995:4968479 INSPEC DN B9507-2550G-035
- Poly(cyclohexyl 2-cyanoacrylate-co-ethoxyethyl 2-cyanoacrylate) as a
- positive tone electron beam resist for **phase-shift mask** fabrication. Tamura, A.; Yonezawa, M. (Electron. Res. Lab., Toppan Printing Co. Ltd., AU Saitama, Japan); Sato, M.; Okuyama, T.
- Proceedings of the SPIE The International Society for Optical Engineering (1994) vol.2254, p.228-36, 4 refs.
 - Price: CCCC 0 8194 1563 4/94/\$6.00 CODEN: PSISDG ISSN: 0277-786X
 - Conference: Photomask and X-Ray Mask Technology, Kanagawa, Japan, 22 April 1994
- Sponsor(s): SPIE; BACUS DТ Conference Article; Journal
- Practical; Experimental
- TC CY United States
- LA. English
- ANSWER 7 OF 7 INSPEC (C) 2003 IEE on STN

- 1992:4311819 INSPEC DN B9302-2550G-046
- Resolution improvement with annular illumination. TT
- MI Tounai, K.; Tanabe, H.; Nozue, H.; Kasama, K. (VLSI Dev. Div., NEC Corp., Kanagawa, Japan)
- Proceedings of the SPIE The International Society for Optical Engineering (1992) vol.1674, pt.2, p.753-64. 5 refs. Price: CCCC 0 8194 0829 8/92/\$4.00
 - CODEN: PSISDG ISSN: 0277-786X
 - Conference: Optical/Laser Microlithography V. San Jose, CA, USA, 11-13 March 1992
- Sponsor(s): SPIE
- DT Conference Article; Journal
- Practical; Experimental

CY United States LA English